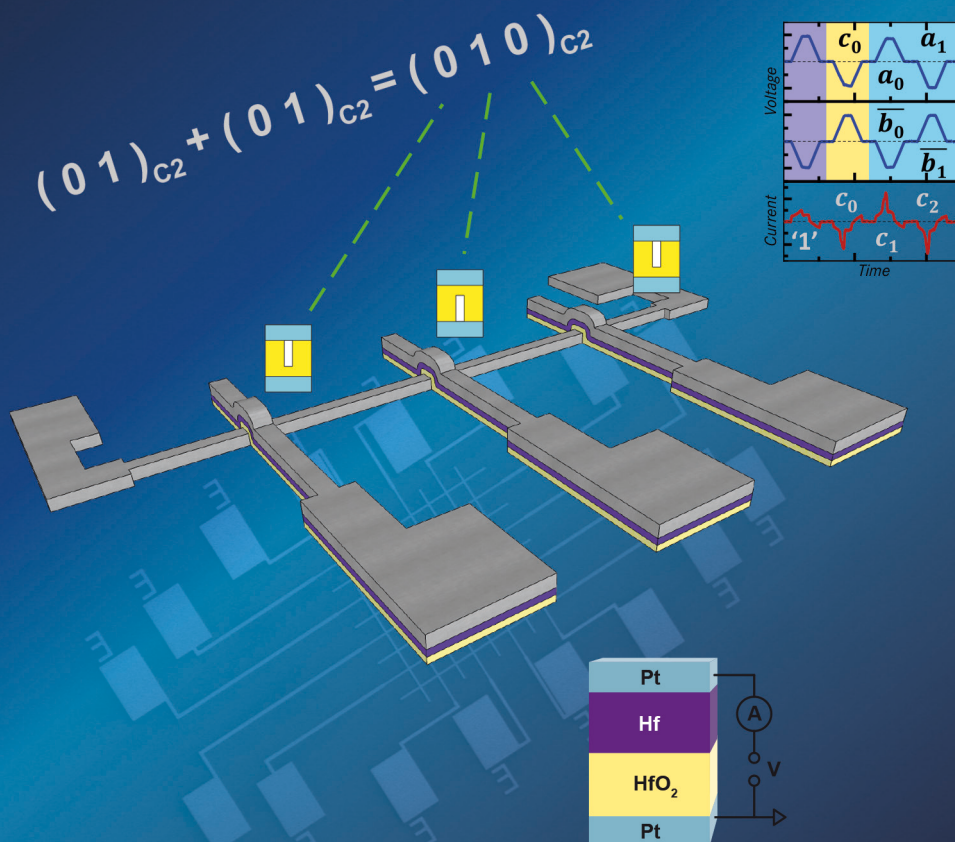


Development of ReRAM-based Devices for Logic- and Computation-in-Memory Applications

Thomas Breuer



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